

## KSP92/93

### High Voltage Transistor



### PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol    | Parameter  | Value     | Units                |
|-----------|--|-----------|----------------------|
| $V_{CBO}$ | Collector-Base Voltage                                 |           |                      |
|           | : KSP92  | -300      | V                    |
|           | : KSP93  | -200      | V                    |
| $V_{CEO}$ | Collector-Emitter Voltage                              |           |                      |
|           | : KSP92  | -300      | V                    |
|           | : KSP93  | -200      | V                    |
| $V_{EBO}$ | Emitter-Base Voltage                                   | -5        | V                    |
| $I_C$     | Collector Current                                      | -500      | mA                   |
| $P_C$     | Collector Power Dissipation ( $T_a=25^\circ\text{C}$ ) | 625       | mW                   |
|           | Derate above $25^\circ\text{C}$                        | 5         | mW/ $^\circ\text{C}$ |
| $P_C$     | Collector Power Dissipation ( $T_C=25^\circ\text{C}$ ) | 1.5       | W                    |
|           | Derate above $25^\circ\text{C}$                        | 12        | mW/ $^\circ\text{C}$ |
| $T_J$     | Junction Temperature                                   | 150       | $^\circ\text{C}$     |
| $T_{STG}$ | Storage Temperature                                    | -55 ~ 150 | $^\circ\text{C}$     |

#### Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol               | Parameter                              | Test Condition  | Min. | Max.   | Units         |
|----------------------|--|---|------|--------|---------------|
| $BV_{CBO}$           | Collector-Base Breakdown Voltage       | $I_C = -100\mu\text{A}, I_E = 0$                              |      |        |               |
|                      | : KSP92                                |   | -300 |        | V             |
|                      | : KSP93                                |   | -200 |        | V             |
| $BV_{CEO}$           | * Collector-Emitter Breakdown Voltage  | $I_C = -1\text{mA}, I_B = 0$                                  |      |        |               |
|                      | : KSP92                                |   | -300 |        | V             |
|                      | : KSP93                                |   | -200 |        | V             |
| $BV_{EBO}$           | Emitter-Base Breakdown Voltage         | $I_E = -100\mu\text{A}, I_C = 0$                              | -5   |        | V             |
| $I_{CBO}$            | Collector Cur-off Current              |   |      |        |               |
|                      | : KSP92                                | $V_{CB} = -200\text{V}, I_E = 0$                              |      | -0.25  | $\mu\text{A}$ |
|                      | : KSP93                                | $V_{CB} = -160\text{V}, I_E = 0$                              |      | -0.25  | $\mu\text{A}$ |
| $I_{EBO}$            | Emitter Cut-off Current                | $V_{EB} = -3\text{V}, I_C = 0$                                |      | -0.10  | $\mu\text{A}$ |
| $h_{FE}$             | * DC Current Gain                      | $V_{CE} = -10\text{V}, I_C = -1\text{mA}$                     | 25   |        |               |
|                      |  | $V_{CE} = -10\text{V}, I_C = -10\text{mA}$                    | 40   |        |               |
|                      |  | $V_{CE} = -10\text{V}, I_C = -30\text{mA}$                    | 25   |        |               |
| $V_{CE}(\text{sat})$ | * Collector-Emitter Saturation Voltage | $I_C = -20\text{mA}, I_B = -2\text{mA}$                       |      | -0.50  | V             |
| $V_{BE}(\text{sat})$ | * Base-Emitter Saturation Voltage      | $I_C = -20\text{mA}, I_B = -2\text{mA}$                       |      | -0.90  | V             |
| $f_T$                | Current Gain Bandwidth Product         | $V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$ | 50   |        | MHz           |
| $C_{ob}$             | Output Capacitance                     |   |      |        |               |
|                      |  | $V_{CB} = -20\text{V}, I_E = 0$<br>$f = 1\text{MHz}$          |      | 6<br>8 | pF<br>pF      |

\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycles  $\leq 2\%$

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## Typical Characteristics

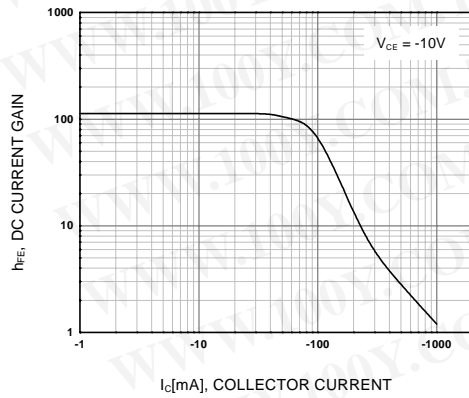


Figure 1. DC current Gain

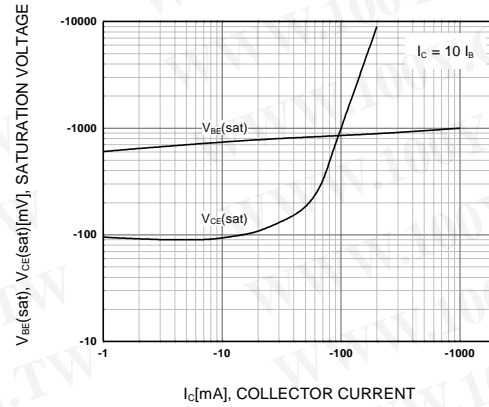


Figure 2. Saturation Voltage

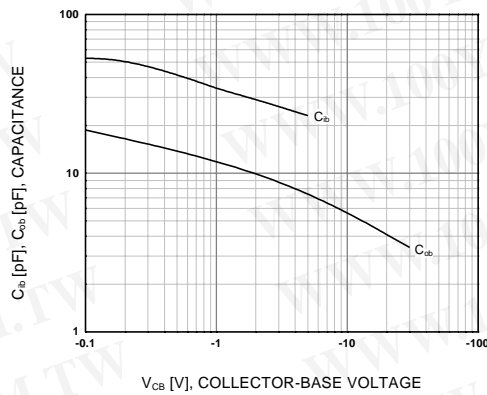


Figure 3. Capacitance

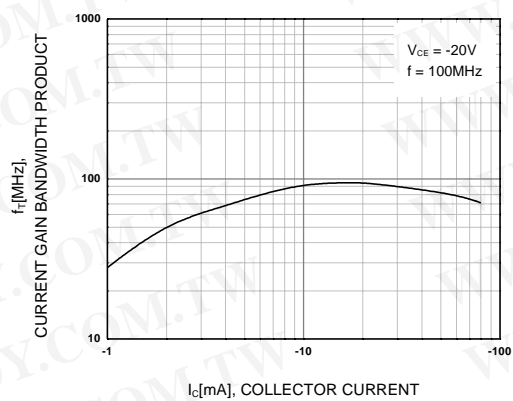


Figure 4. Current Gain Bandwidth Product

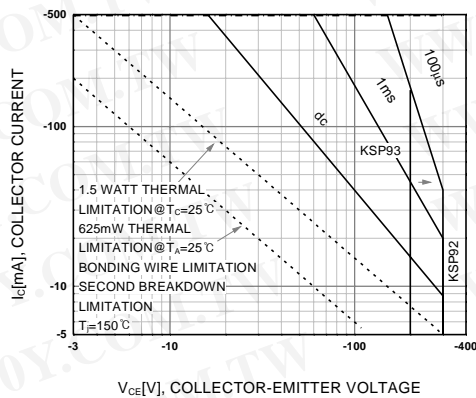


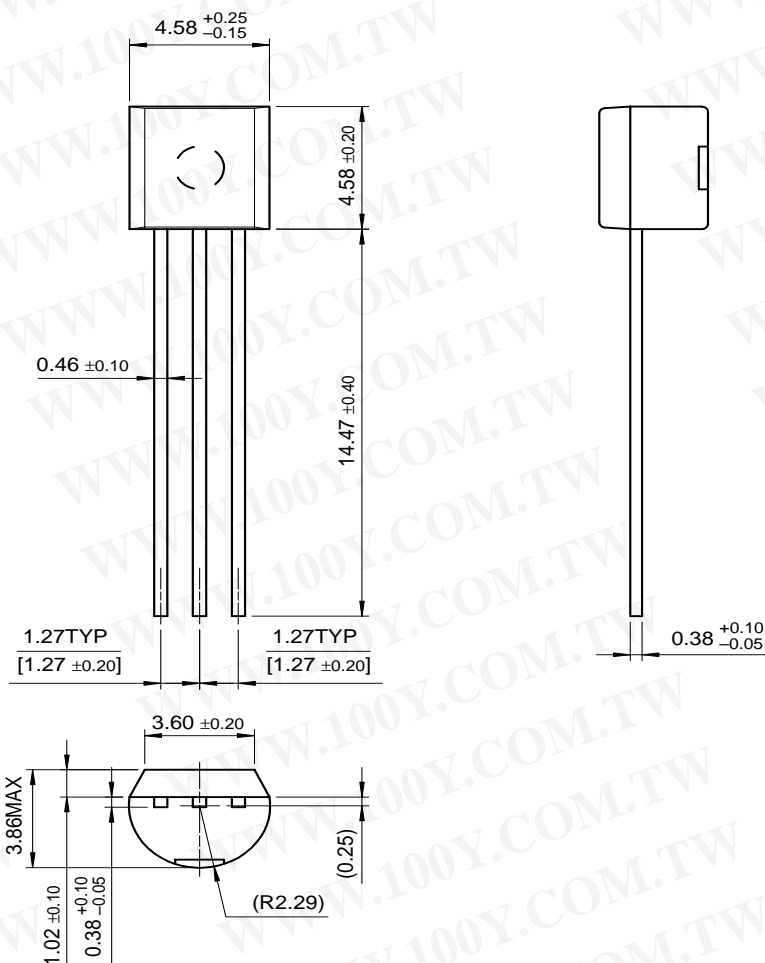
Figure 5. Active-Region Safe Operating Area

## Package Dimensions

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TO-92



Dimensions in Millimeters

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